PACE 2/8 * RCVD AT 2/13/2004 1:37:36 PM [Eastern Standard Time] * SVR:USPTO-EFXRF-1/2 * DNIS:8729306 * CSID:518 449 0047 * DURATION (mm-5s):02-14

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE Applicant: Letavic et al. Application No.: 10/015,847 Filed: 12/10/2001 For: DUAL GATE OXIDE HIGH-VOLTAGE SEMICONDUCTOR DEVICE PRECEIVED CENTRAL FAX CENTER FEB 1 3 2004 FOR DUAL GATE OXIDE HIGH-VOLTAGE SEMICONDUCTOR DEVICE

Mail Stop Non-Fee Amendments Commissioner for Patents P.O. Box 1450 Alexandria VA 22313-1450

AMENDMENT

Sir:

In response to the Office Action of November 18, 2003, please amend the aboveidentified application as follows: